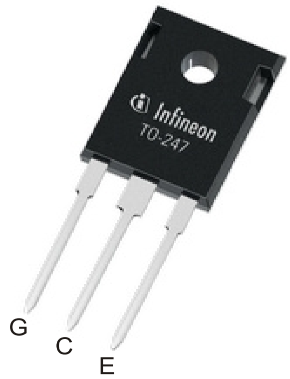
THE DATASHEET OF

IKW25N120H3FKSA1

High speed DuoPack: IGBT in Trench and Fieldstop technology with soft, fast recovery antiparallel diode



Features

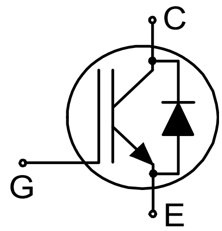
- V_{CE} = 1200 V
- I_C = 25 A
- Very low $V_{CE,sat}$
- Low EMI
- Very soft, fast recovery antiparallel diode
- Maximum junction temperature T_{vjmax} = 175°C
- Qualified according to JEDEC for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models: http://www.infineon.com/igbt/

Potential applications

- Uninterruptible power supplies
- Welding converters
- Converters with high switching frequency

Lead-Free
Green
Halogen-Free
RoHS

Description



Type	Package	Marking
IKW25N120H3	PG-TO247-3	K25H1203

Table of contents

1 Package

Table 1 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Internal emitter inductance measured 5 mm (0.197 in) from case	L_E			13.0		nH
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature		wave soldering 1.6 mm (0.063 in.) from case for 10 s			260	°C
Mounting torque, M3 screw Maximum of mounting processes: 3	M				0.6	Nm
Thermal resistance, junction-ambient	$R_{th(j-a)}$				40	K/W

2 IGBT

Table 2 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CE}			1200	V
DC collector current, limited by T_{vjmax}	I_C		T_c = 25 °C	50	A
			T_c = 100 °C	25	
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpuls}			100	A
Turn-off safe operating area		$V_{CE} \leq$ 1200 V, $T_{vj} \leq$ 175 °C		100	A
Gate-emitter voltage	V_{GE}			±20	V
Short circuit withstand time	t_{SC}	$V_{CC} \leq$ 600 V, Allowed number of short circuits < 1000, Time between short circuits ≥ 1.0 s, T_{vj} = 175 °C		10	µs
Power dissipation	P_{tot}		T_c = 25 °C	326	W
			T_c = 100 °C	156	

Table 3 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter breakdown voltage	V_{BRCES}	I_C = 0.5 mA, V_{GE} = 0 V	1200			V

Table 3 Characteristic values (continued)

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\,sat}$	I_C = 25.0 A, V_{GE} = 15 V	T_{vj} = 25 °C		2.05	2.40	V
			T_{vj} = 125 °C		2.50		
			T_{vj} = 175 °C		2.70		
Gate-emitter threshold voltage	V_{GEth}	I_C = 0.85 mA, V_{CE} = V_{GE}		5.00	5.80	6.50	V
Zero gate voltage collector current	I_{CES}	V_{CE} = 1200 V, V_{GE} = 0 V	T_{vj} = 25 °C			250	µA
			T_{vj} = 175 °C			2500	
Gate-emitter leakage current	I_{GES}	V_{CE} = 0 V, V_{GE} = 20 V				600	nA
Transconductance	g_{fs}	I_C = 25.0 A, V_{CE} = 20 V			13.0		S
Short circuit collector current	I_{SC}	$V_{CC} \leq$ 600 V, V_{GE} = 15 V, $t_{SC} \leq$ 10 µs, Allowed number of short circuits < 1000 , Time between short circuits ≥ 1.0 s, T_{vj} = 175 °C			87		A
Input capacitance	C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1000 kHz			1430		pF
Output capacitance	C_{oes}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1000 kHz			115		pF
Reverse transfer capacitance	C_{res}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1000 kHz			75		pF
Gate charge	Q_G	I_C = 25.0 A, V_{GE} = 15 V, V_{CE} = 960 V			115		nC
Turn-on delay time	t_{don}	V_{CE} = 600 V, V_{GE} = +0/+15 V, R_{Gon} = 23.0 Ω, R_{Goff} = 23.0 Ω, L_σ = 80 nH, C_σ = 67 pF	T_{vj} = 25 °C, I_C = 25.0 A		27		ns
			T_{vj} = 175 °C, I_C = 25.0 A		26		
Rise time (inductive load)	t_r	V_{CE} = 600 V, V_{GE} = +0/+15 V, R_{Gon} = 23.0 Ω, R_{Goff} = 23.0 Ω, L_σ = 80 nH, C_σ = 67 pF	T_{vj} = 25 °C, I_C = 25.0 A		41		ns
			T_{vj} = 175 °C, I_C = 25.0 A		35		
Turn-off delay time	t_{doff}	V_{CE} = 600 V, V_{GE} = +0/+15 V, R_{Gon} = 23.0 Ω, R_{Goff} = 23.0 Ω, L_σ = 80 nH, C_σ = 67 pF	T_{vj} = 25 °C, I_C = 25.0 A		277		ns
			T_{vj} = 175 °C, I_C = 25.0 A		347		
Fall time (inductive load)	t_f	V_{CE} = 600 V, V_{GE} = +0/+15 V, R_{Gon} = 23.0 Ω, R_{Goff} = 23.0 Ω, L_σ = 80 nH, C_σ = 67 pF	T_{vj} = 25 °C, I_C = 25.0 A		17		ns
			T_{vj} = 175 °C, I_C = 25.0 A		50		

Table 3 Characteristic values (continued)

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Turn-on energy	E_{on}	V_{CE} = 600 V, V_{GE} = +0/+15 V, R_{Gon} = 23.0 Ω, R_{Goff} = 23.0 Ω, $L_σ$ = 80 nH, $C_σ$ = 67 pF	T_{vj} = 25 °C, I_C = 25.0 A		1.80		mJ
			T_{vj} = 175 °C, I_C = 25.0 A		2.60		
Turn-off energy	E_{off}	V_{CE} = 600 V, V_{GE} = +0/+15 V, R_{Gon} = 23.0 Ω, R_{Goff} = 23.0 Ω, $L_σ$ = 80 nH, $C_σ$ = 67 pF	T_{vj} = 25 °C, I_C = 25.0 A		0.85		mJ
			T_{vj} = 175 °C, I_C = 25.0 A		1.70		
Total switching energy	E_{ts}	V_{CE} = 600 V, V_{GE} = +0/+15 V, R_{Gon} = 23.0 Ω, R_{Goff} = 23.0 Ω, $L_σ$ = 80 nH, $C_σ$ = 67 pF	T_{vj} = 25 °C, I_C = 25.0 A		2.65		mJ
			T_{vj} = 175 °C, I_C = 25.0 A		4.30		
IGBT thermal resistance, junction-case	R_{thjc}					0.46	K/W
Operating junction temperature	T_{vj}			-40		175	°C

Note: *Electrical Characteristic, at T_{vj} = 25°C, unless otherwise specified.*

3 Diode

Table 4 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}			1200	V
Diode forward current, limited by T_{vjmax}	I_F		T_c = 25 °C	25	A
			T_c = 100 °C	12.5	
Diode pulsed current, limited by T_{vjmax}	I_{Fpuls}			100	A

Table 5 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Diode forward voltage	V_F	I_F = 12.5 A	T_{vj} = 25 °C		1.80	2.35	V
			T_{vj} = 175 °C		1.85		

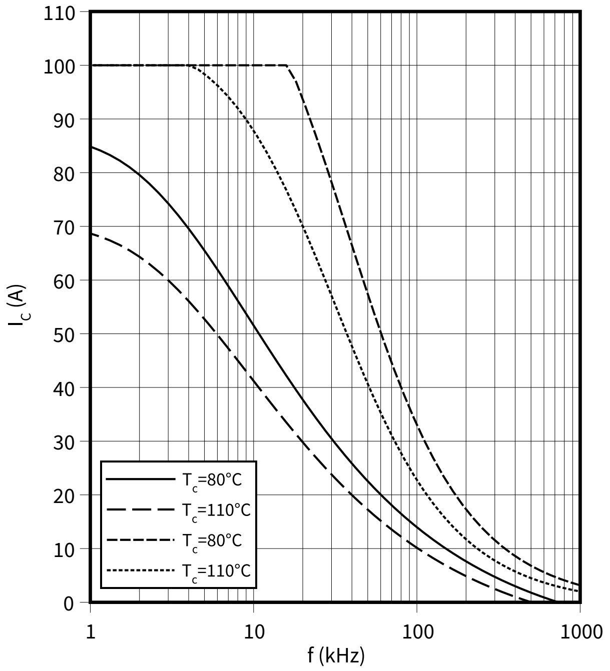
Table 5 **Characteristic values (continued)**

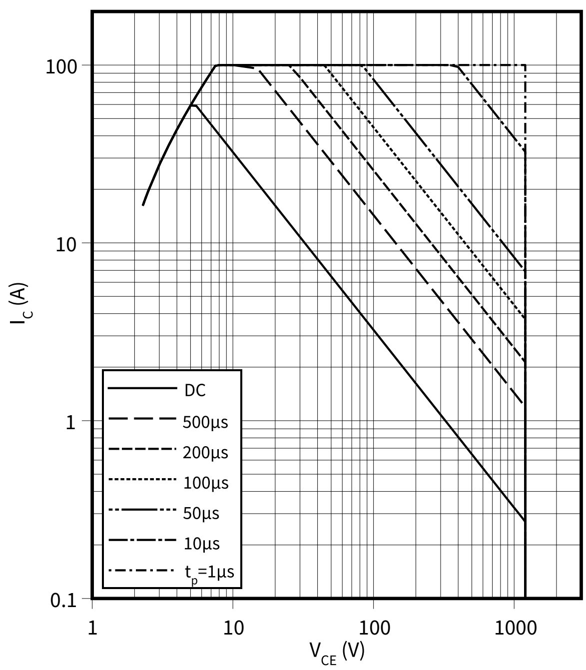
Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Diode forward voltage	V_F	I_F = 25.0 A	T_{vj} = 25 °C		2.40	3.05	V
			T_{vj} = 125 °C		2.60		
			T_{vj} = 175 °C		2.60		
Reverse leakage current	I_R	V_R = 1200 V	T_{vj} = 25 °C			250	µA
			T_{vj} = 175 °C			2500	
Diode reverse recovery time	t_{rr}	V_R = 600 V	T_{vj} = 25 °C, I_F = 25.0 A, $-di_F/dt$ = 500 A/µs		290		ns
			T_{vj} = 175 °C, I_F = 25.0 A, $-di_F/dt$ = 500 A/µs		505		
Diode reverse recovery charge	Q_{rr}	V_R = 600 V	T_{vj} = 25 °C, I_F = 25.0 A, $-di_F/dt$ = 500 A/µs		1.20		µC
			T_{vj} = 175 °C, I_F = 25.0 A, $-di_F/dt$ = 500 A/µs		2.75		
Diode peak reverse recovery current	I_{rrm}	V_R = 600 V	T_{vj} = 25 °C, I_F = 25.0 A, $-di_F/dt$ = 500 A/µs		10.4		A
			T_{vj} = 175 °C, I_F = 25.0 A, $-di_F/dt$ = 500 A/µs		12.8		
Diode peak rate off fall of reverse recovery current	dI_{rr}/dt	V_R = 600 V	T_{vj} = 25 °C, I_F = 25.0 A, $-di_F/dt$ = 500 A/µs		-150		A/µs
			T_{vj} = 175 °C, I_F = 25.0 A, $-di_F/dt$ = 500 A/µs		-85		
Diode thermal resistance, junction-case	R_{thjc}					1.49	K/W
Operating junction temperature	T_{vj}			-40		175	°C

Note: *For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.*

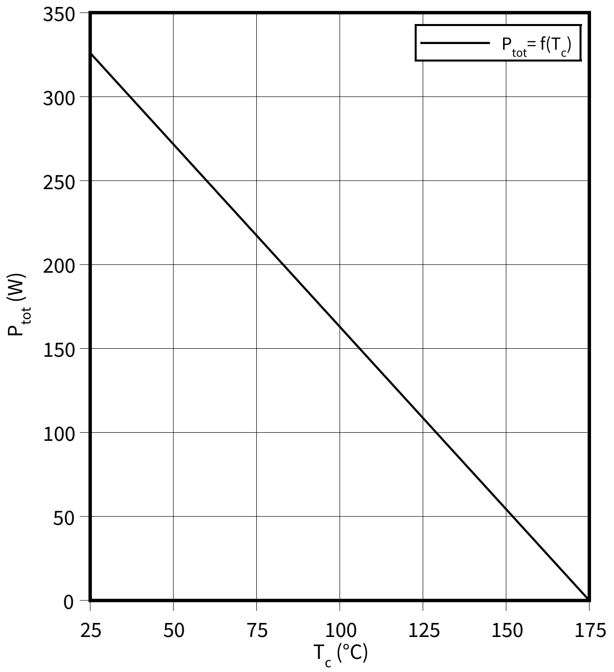
4 Characteristics diagrams

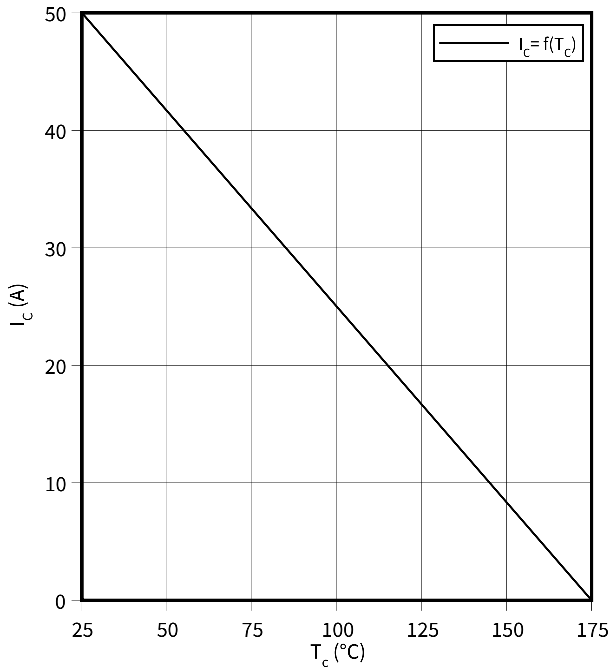
Collector current as a function of switching frequency, IGBT	Forward bias safe operating area, IGBT
$I_C = f(f)$ $D = 0.5$, $V_{CE} = 600$ V, $T_{vj} \leq 175$ °C, $V_{GE} = 0/15$ V, $R_G = 23\ \Omega$	$I_C = f(V_{CE})$ $D = 0$, $T_{vj} \leq 175$ °C, $V_{GE} = 15$ V, $T_c = 25$ °C



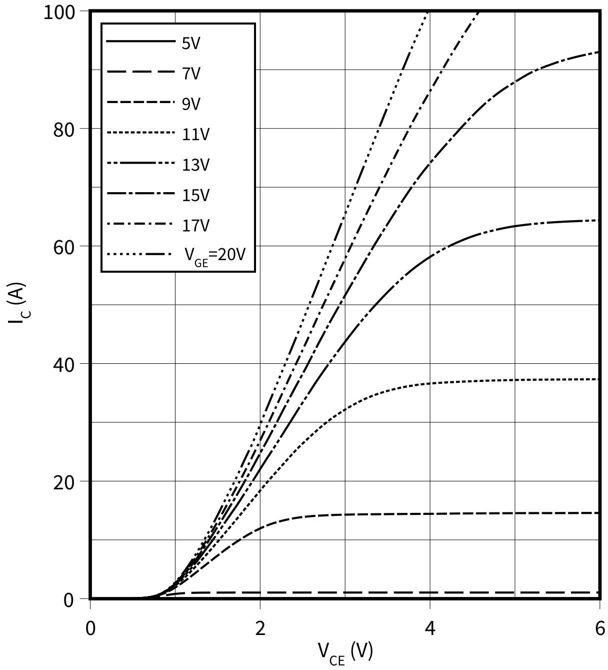


Power dissipation as a function of case temperature, IGBT	Collector current as a function of case temperature, IGBT
$P_{tot} = f(T_c)$ $T_{vj} \leq 175$ °C	$I_C = f(T_c)$ $V_{GE} \geq 15$ V, $T_{vj} \leq 175$ °C

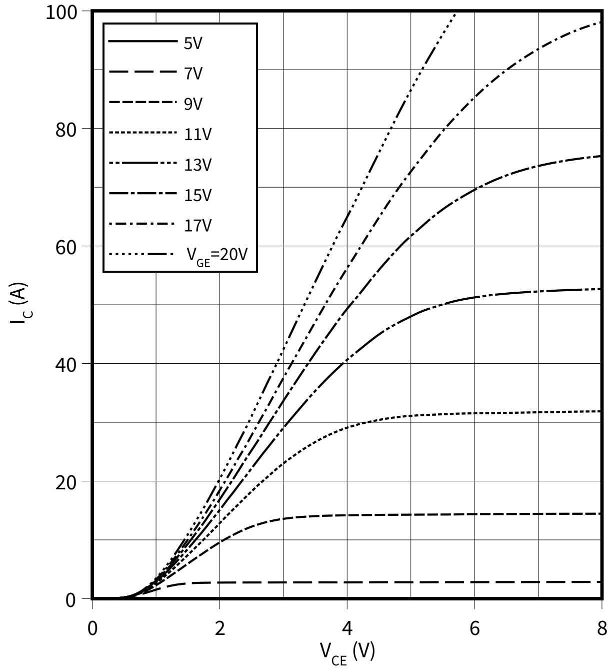




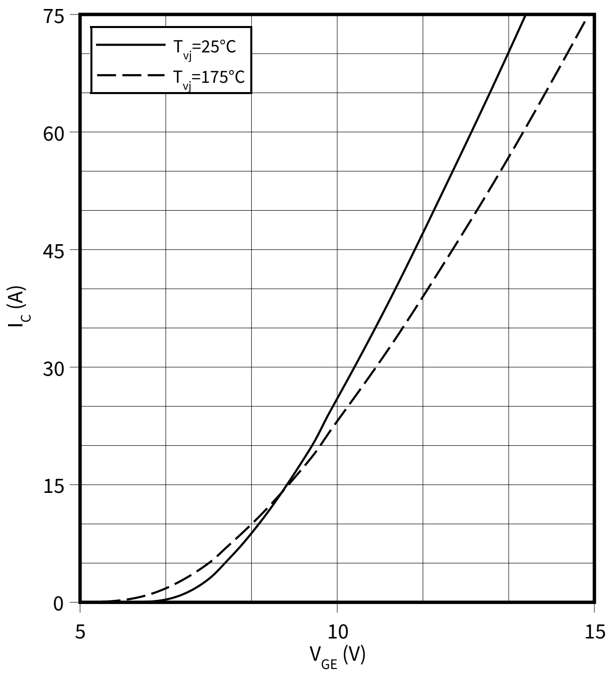
Typical output characteristic, IGBT
$I_C = f(V_{CE})$
$T_{vj} = 25\ °C$



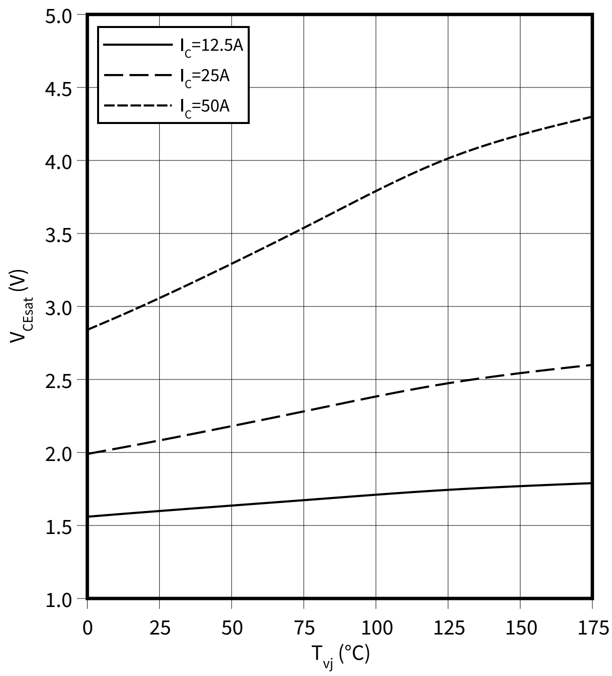
Typical output characteristic, IGBT
$I_C = f(V_{CE})$
$T_{vj} = 175\ °C$



Typical transfer characteristic, IGBT
$I_C = f(V_{GE})$
$V_{CE} = 20\ V$



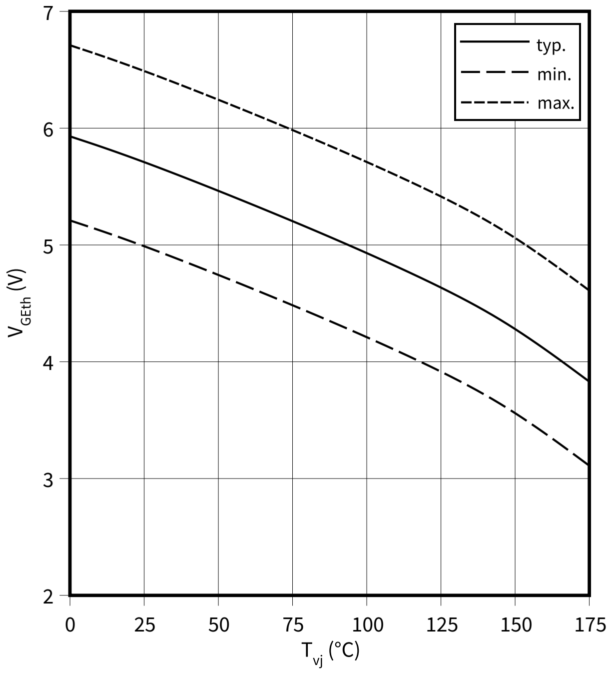
Typical collector-emitter saturation voltage as a function of junction temperature, IGBT
$V_{CEsat} = f(T_{vj})$
$V_{GE} = 15\ V$



Gate-emitter threshold voltage as a function of junction temperature, IGBT

$V_{GEth} = f(T_{vj})$

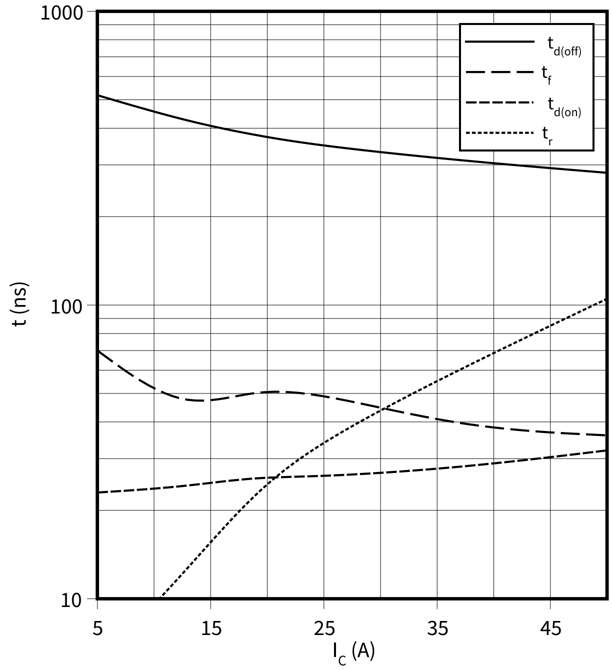
$I_C = 0.85$ mA



Typical switching times as a function of collector current, IGBT

$t = f(I_C)$

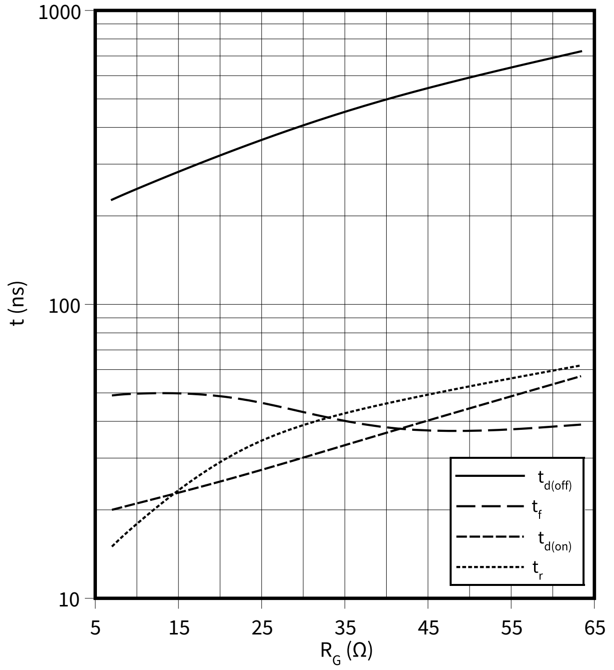
$V_{CE} = 600$ V, $T_{vj} = 175$ °C, $V_{GE} = 0/15$ V, $R_G = 23\ \Omega$



Typical switching times as a function of gate resistance, IGBT

$t = f(R_G)$

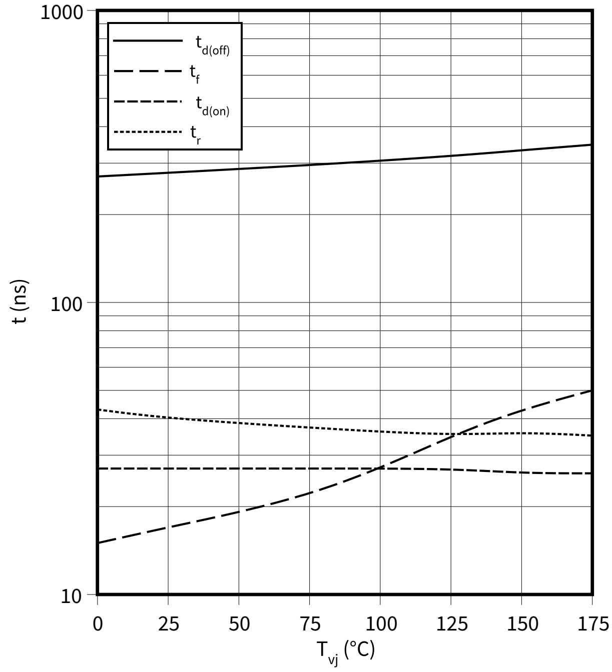
$I_C = 25.0$ A, $V_{CE} = 600$ V, $T_{vj} = 175$ °C, $V_{GE} = 0/15$ V



Typical switching times as a function of junction temperature, IGBT

$t = f(T_{vj})$

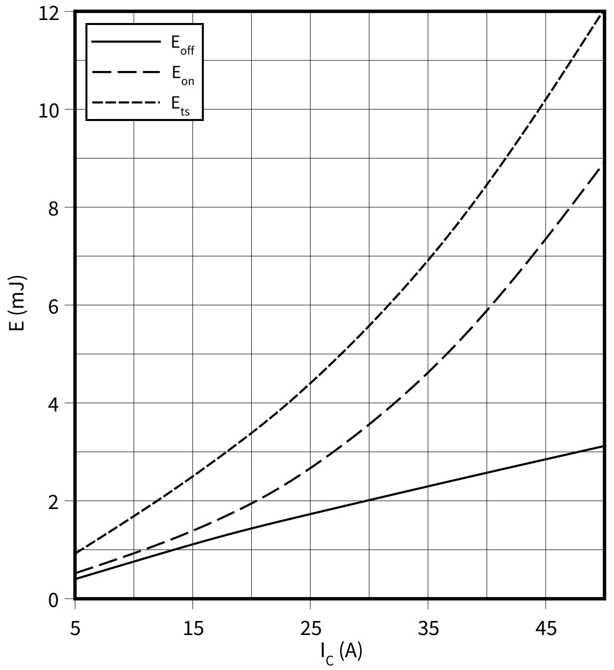
$I_C = 25.0$ A, $V_{CE} = 600$ V, $V_{GE} = 0/15$ V, $R_G = 23\ \Omega$



Typical switching energy losses as a function of collector current, IGBT

$E = f(I_C)$

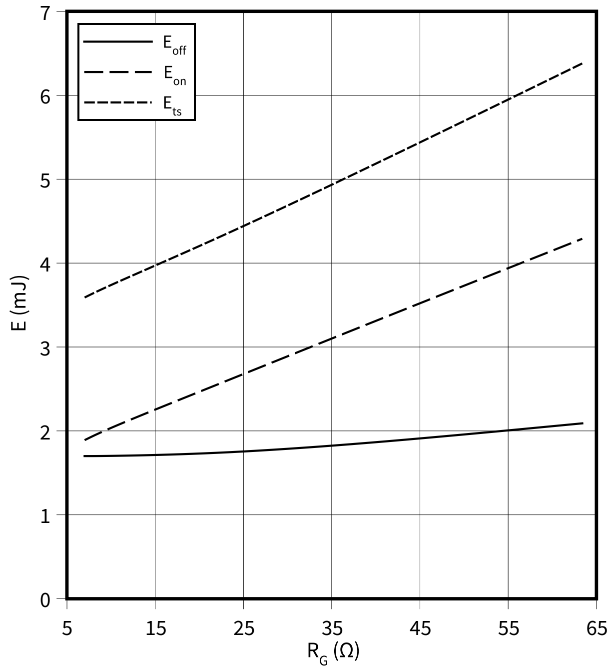
V_{CE} = 600 V, T_{vj} = 175 °C, V_{GE} = 0/15 V, R_G = 23 Ω



Typical switching energy losses as a function of gate resistance, IGBT

$E = f(R_G)$

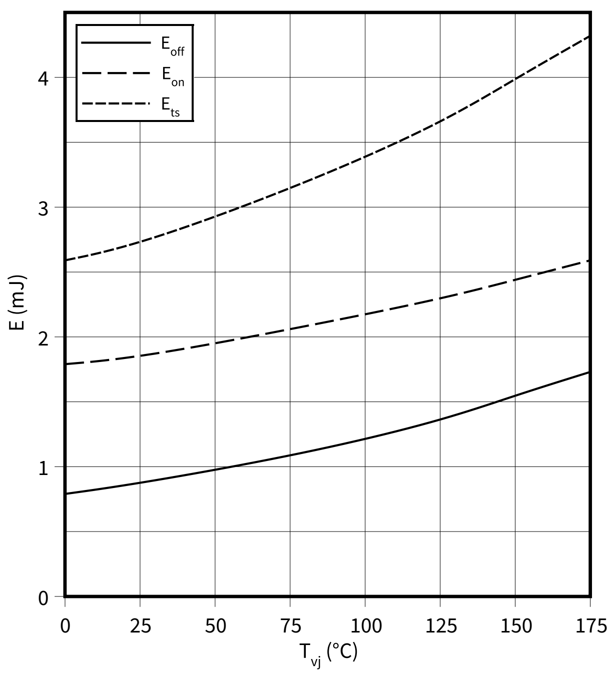
I_C = 25.0 A, V_{CE} = 600 V, T_{vj} = 175 °C, V_{GE} = 0/15 V



Typical switching energy losses as a function of junction temperature, IGBT

$E = f(T_{vj})$

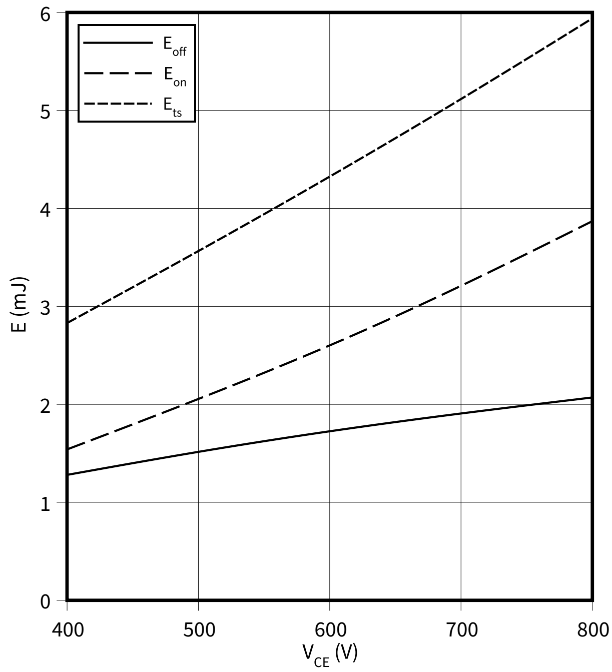
I_C = 25.0 A, V_{CE} = 600 V, V_{GE} = 0/15 V, R_G = 23 Ω



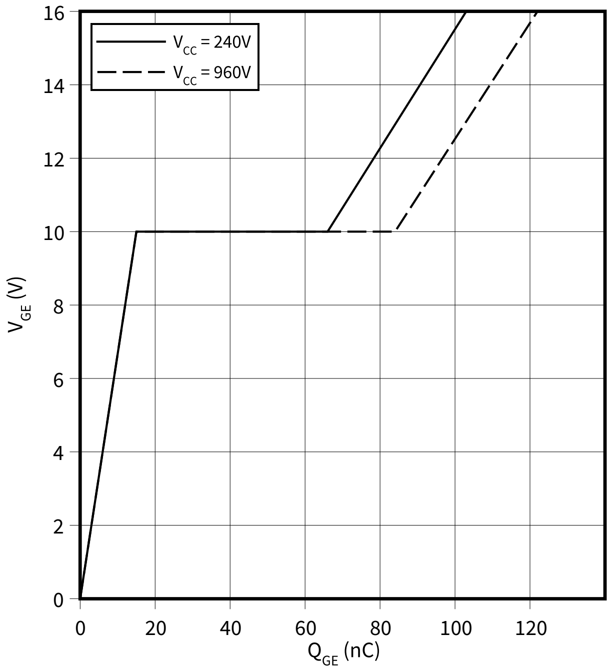
Typical switching energy losses as a function of collector emitter voltage, IGBT

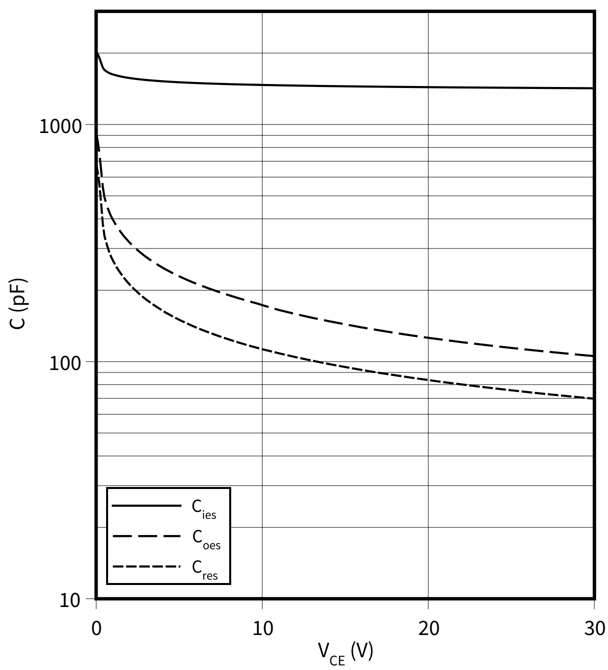
$E = f(V_{CE})$

I_C = 25.0 A, T_{vj} = 175 °C, V_{GE} = 0/15 V, R_G = 23 Ω

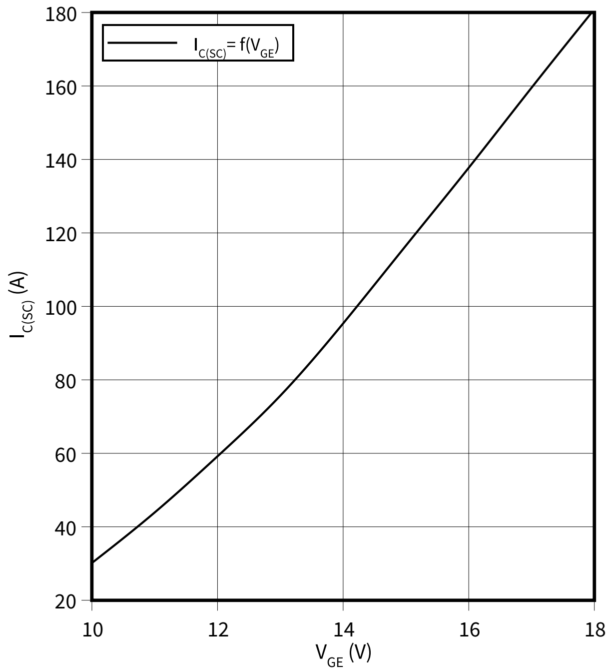


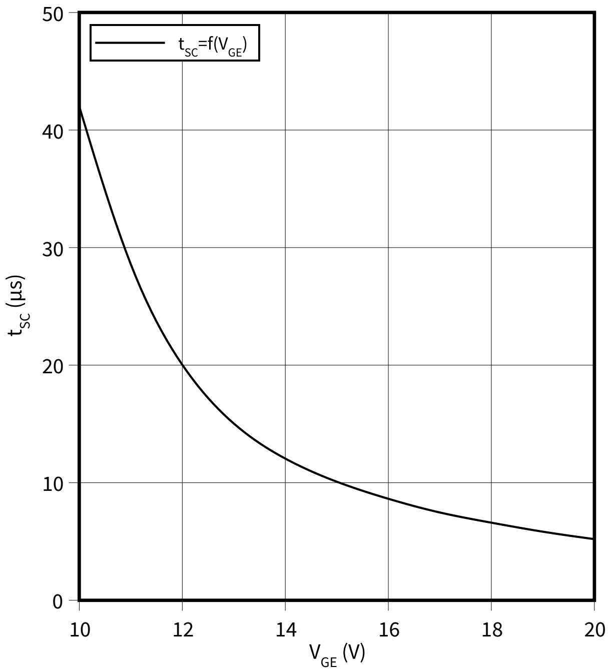
Typical gate charge, IGBT $V_{GE} = f(Q_{GE})$ $I_C = 25.0$ A	Typical capacitance as a function of collector-emitter voltage, IGBT $C = f(V_{CE})$ f = 1000 kHz, $V_{GE} = 0$ V





Typical short circuit collector current as a function of gate-emitter voltage, IGBT $I_{C(SC)} = f(V_{GE})$ $V_{CE} \leq 600$ V, $T_{vj,\ start} = 25$ °C	Short circuit withstand time as a function of gate-emitter voltage, IGBT $t_{SC} = f(V_{GE})$ $T_{vj} \leq 175$ °C, $V_{CC} \leq 600$ V

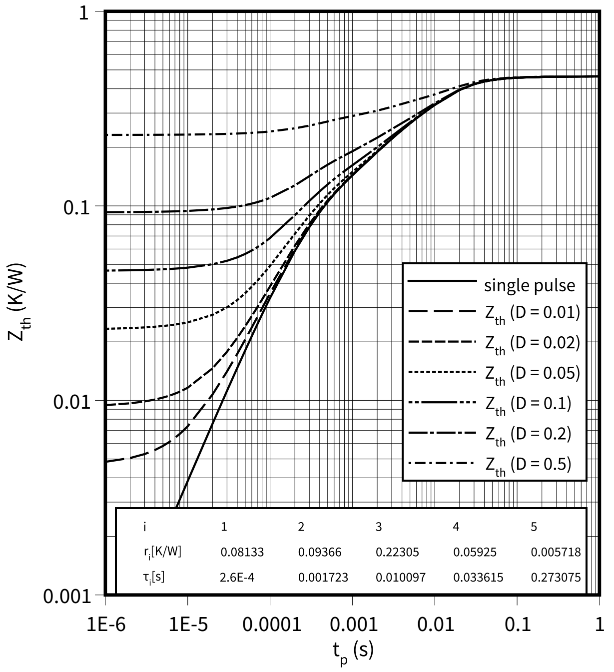




IGBT transient thermal impedance, IGBT

$Z_{th} = f(t_p)$

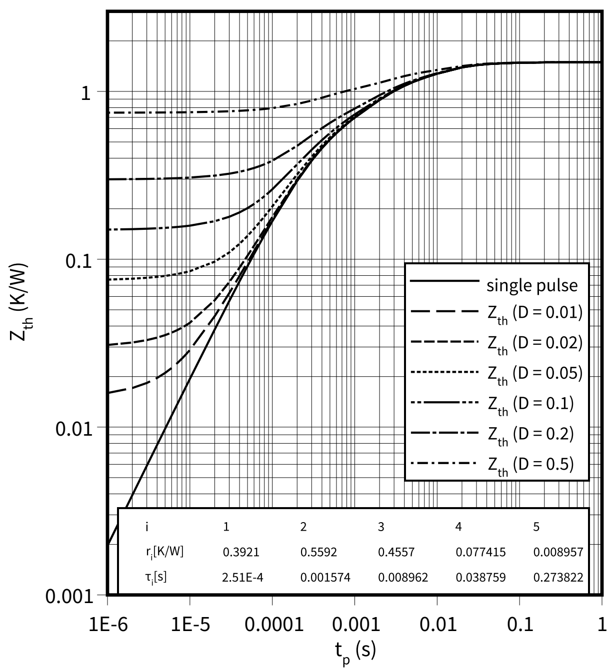
$D = t_p/T$



Diode transient thermal impedance as a function of pulse width, Diode

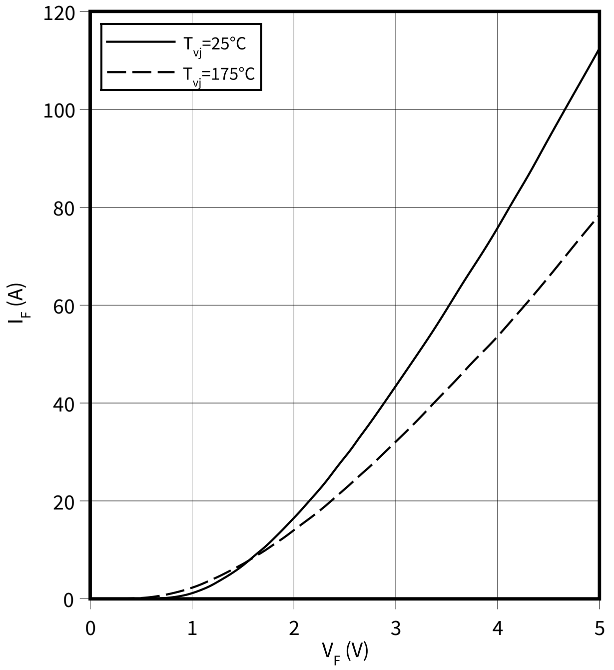
$Z_{th} = f(t_p)$

$D = t_p/T$



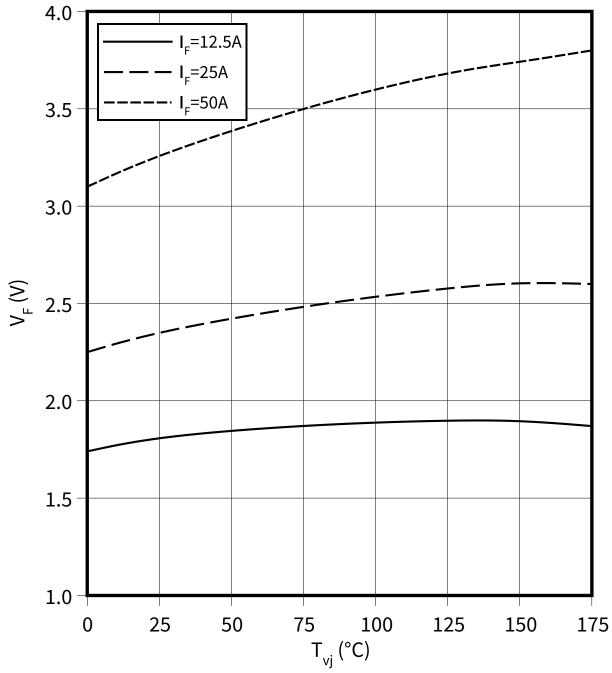
Typical diode forward current as a function of forward voltage, Diode

$I_F = f(V_F)$



Typical diode forward voltage as a function of junction temperature, Diode

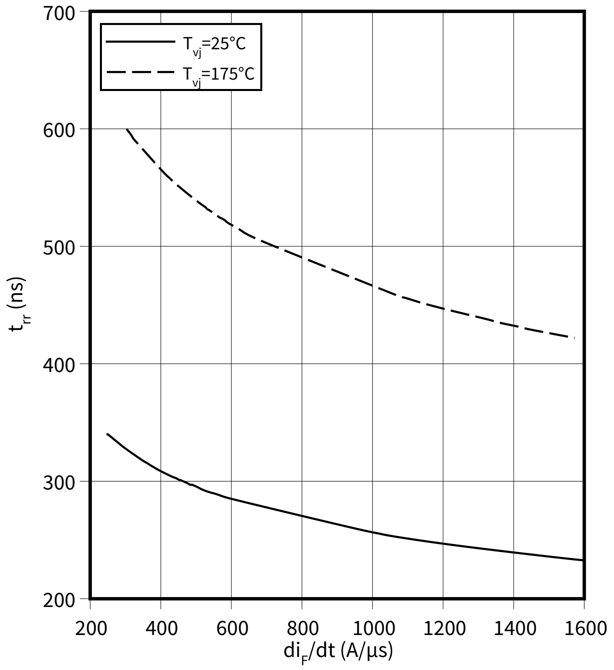
$V_F = f(T_{vj})$



Typical reverse recovery time as a function of diode current slope, Diode

$t_{rr} = f(di_F/dt)$

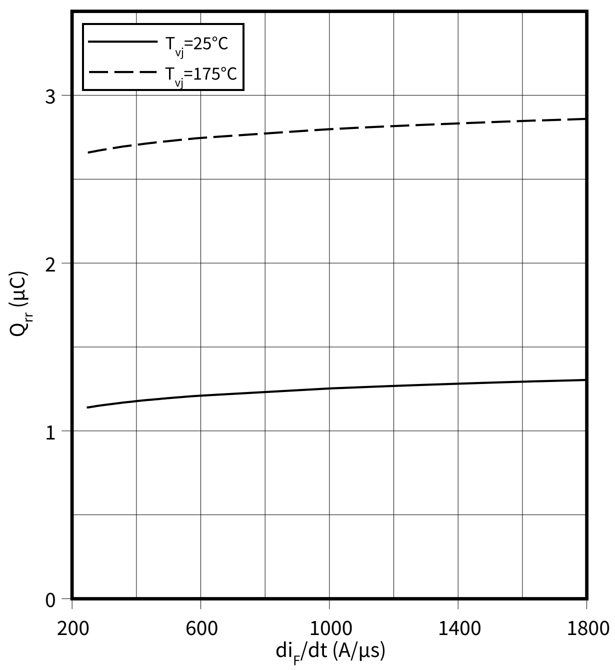
$V_R = 600\ V, I_F = 25\ A$



Typical reverse recovery charge as a function of diode current slope, Diode

$Q_{rr} = f(di_F/dt)$

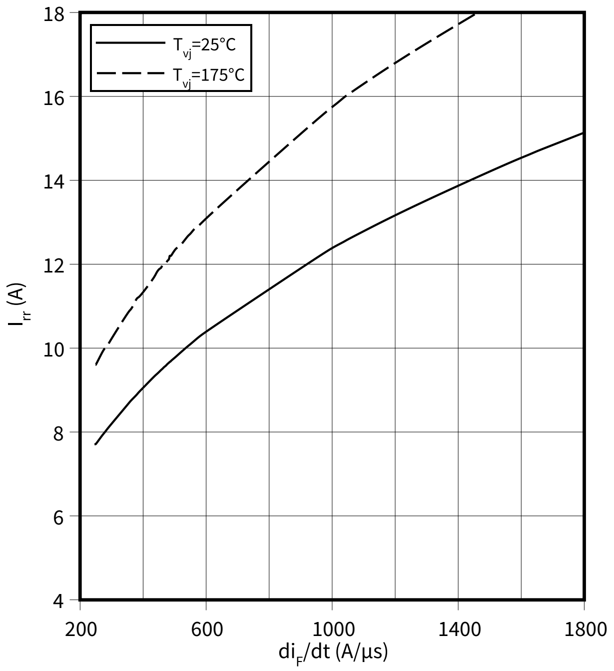
$V_R = 600\ V, I_F = 25\ A$



Typical reverse recovery current as a function of diode current slope, Diode

$I_{rr} = f(di_F/dt)$

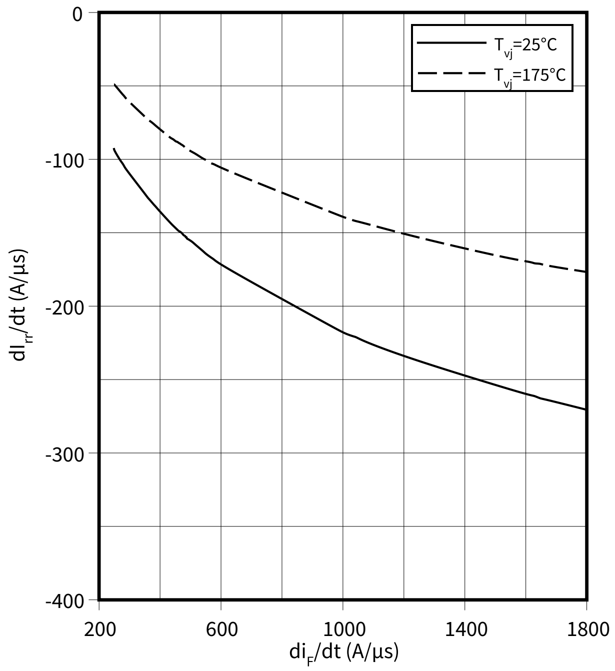
$V_R = 600\ V, I_F = 25\ A$



Typical diode peak rate of fall of reverse recovery current as a function of diode current slope, Diode

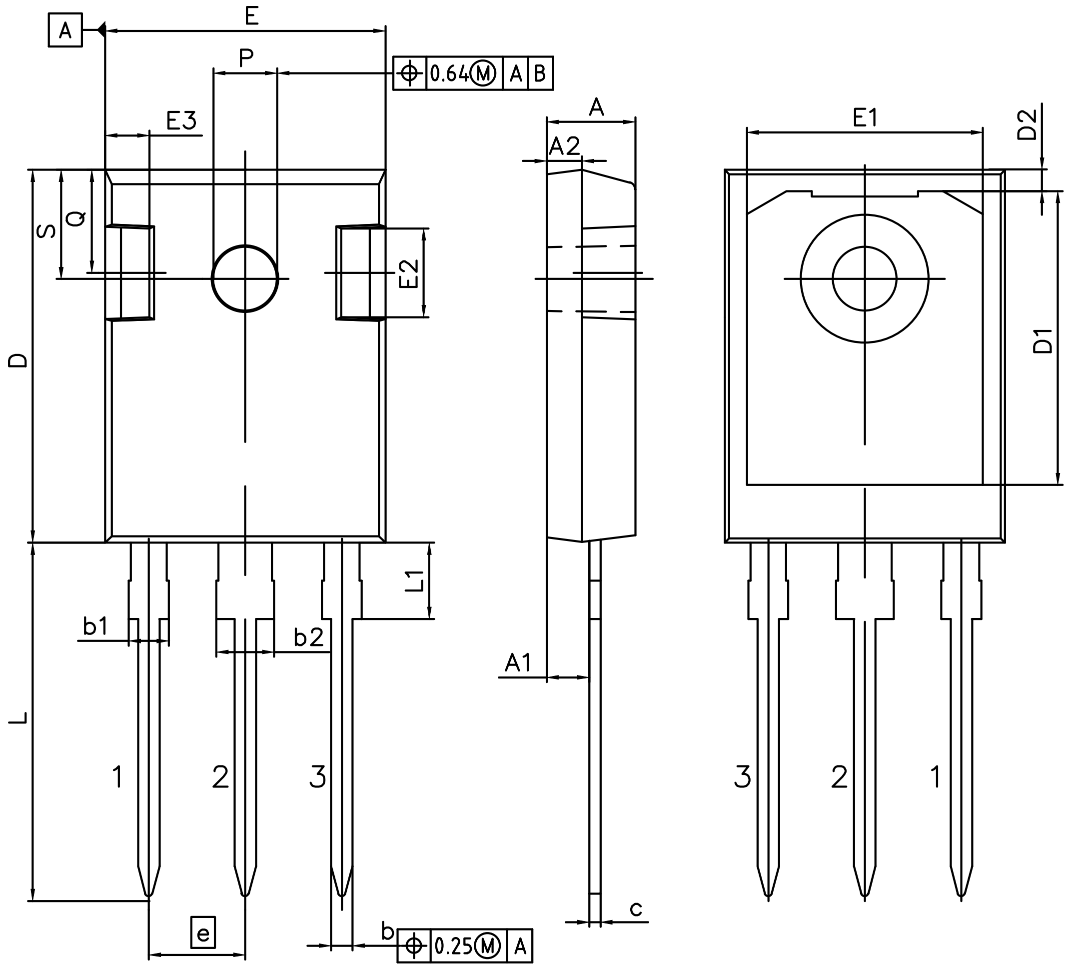
$dI_{rr}/dt = f(di_F/dt)$

$V_R = 600\ V, I_F = 25\ A$



5 Package outlines

Package Drawing PG-TO247-3



DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	4.70	5.30
A1	2.20	2.60
A2	1.50	2.50
b	1.00	1.40
b1	1.60	2.41
b2	2.57	3.43
c	0.38	0.89
D	20.70	21.50
D1	13.08	17.65
D2	0.51	1.35
E	15.50	16.30
E1	12.38	14.15
E2	3.40	5.10
E3	1.00	2.60
e	5.44	
L	19.80	20.40
L1	3.85	4.50
P	3.50	3.70
Q	5.35	6.25
S	6.04	6.30

DOCUMENT NO. Z8B00003327
REVISION 06
SCALE 3:1 0 1 2 3 4 5mm
EUROPEAN PROJECTION
ISSUE DATE 25.07.2018

Figure 6

6 Testing conditions

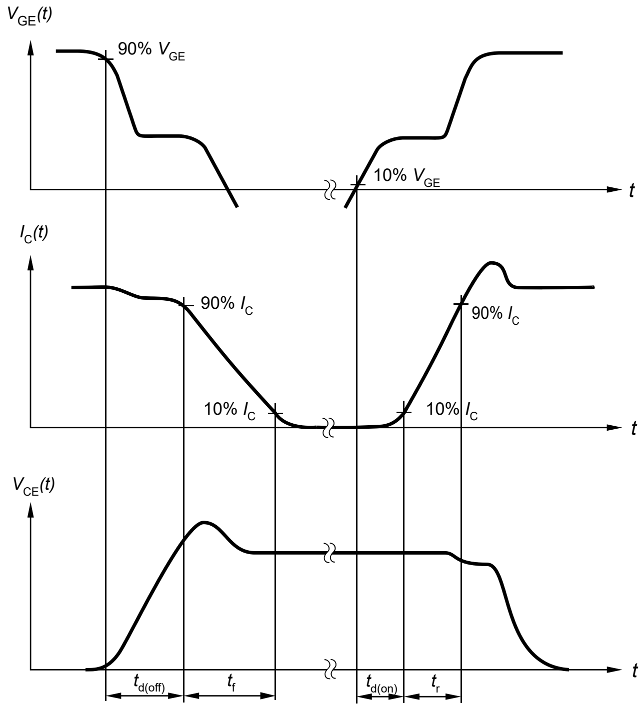


Figure A. **Definition of switching times**

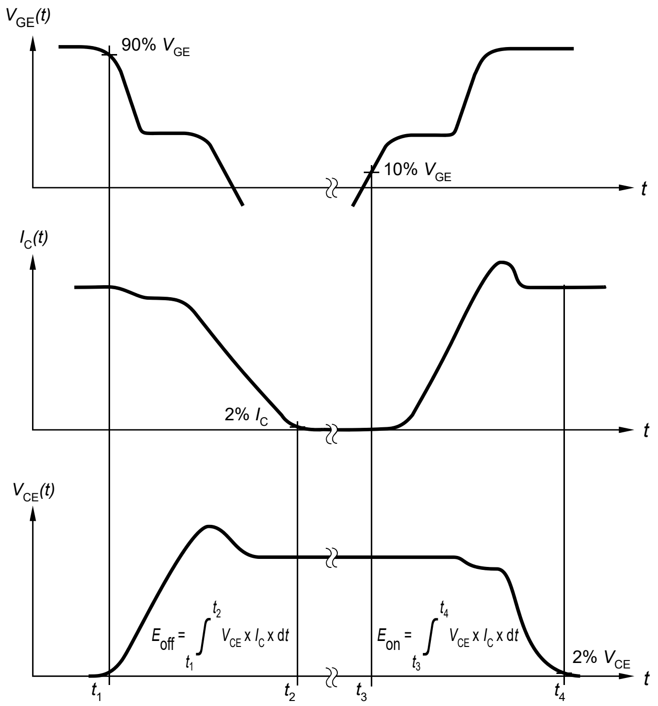


Figure B. **Definition of switching losses**

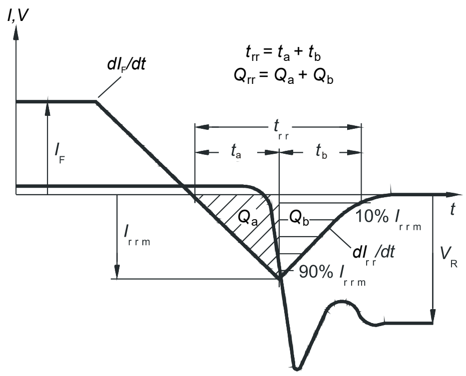


Figure C. **Definition of diode switching characteristics**

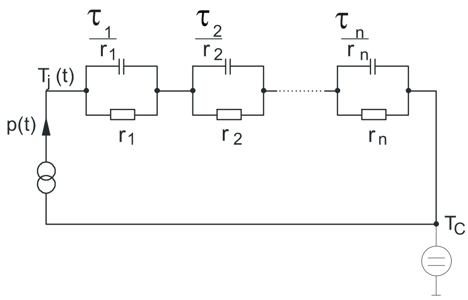


Figure D. **Thermal equivalent circuit**

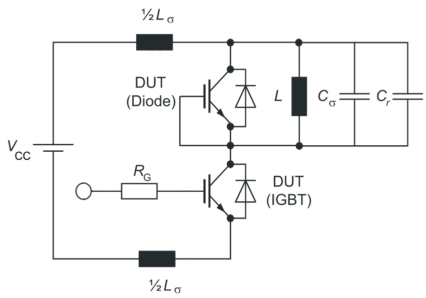


Figure E. **Dynamic test circuit**
Parasitic inductance L_σ,
parasitic capacitor C_σ,
relief capacitor C_r,
(only for ZVT switching)

Figure 7

Revision history

Document revision	Date of release	Description of changes
V1.1	2009-11-27	
V1.2	2010-02-10	
V2.1	2014-12-01	Final data sheet
V2.2		Minor change figure 28
1.00	2021-09-08	Update of legend at the diagram $V_F = f(T_{vj})$

Trademarks

All referenced product or service names and trademarks are the property of their respective owners.

Edition 2021-09-08

Published by

Infineon Technologies AG

81726 Munich, Germany

Do you have a question about any aspect of this document?

Email: erratum@infineon.com

Document reference
IFX-AAK486-005